EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S102	16	(((quantum near2 well) or QW) with (strain$3 or stain$3)) and ((light ADJ3 emit$4 ADJ3 device) or (light-emit$4 ADJ3 device) or LED) and active and clad$4 and substrate and (barrier near3 (InGaP or InGaAsP or GaAsP)) and (guide near2 (layer or medium or region or film))	USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2006/03/03 11:46
S107	0	(kenneth near3 vilhelmsson).in.	USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2006/03/03 11:55
S92	65	ekawa.in.	USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2006/03/03 11:55
S110	0	((((quantum near2 well) or QW) with (strain$3 or stain$3)) and ((light ADJ3 emit$4 ADJ3 device) or (light-emit$4 ADJ3 device) or LED) and active and clad$4 and substrate and (barrier near3 (InGaP or InGaAsP or GaAsP)) and (guide near2 (layer or medium or region or film))).clm.	US-PGPUB	AND	ON	2006/03/03 11:56
S109	0	(kenneth near3 vilhelmsson).in. and "372"/$.ccls.	US-PGPUB	AND	ON	2006/03/03 11:56
S108	1	(kenneth near3 vilhelmsson).in.	US-PGPUB	AND	ON	2006/03/03 11:56
S106	1	(((quantum near2 well) or QW) with (strain$3 or stain$3)) and ((light ADJ3 emit$4 ADJ3 device) or (light-emit$4 ADJ3 device) or LED) and active and clad$4 and substrate and (barrier near3 (InGaP or InGaAsP or GaAsP)) and (guide near2 (layer or medium or region or film))	USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2006/03/03 11:56
S105	32	(((quantum near2 well) or QW) with (strain$3 or stain$3)) and ((light ADJ3 emit$4 ADJ3 device) or (light-emit$4 ADJ3 device) or LED) and active and clad$4 and substrate and (barrier near3 (InGaP or InGaAsP or GaAsP)) and (guide near2 (layer or medium or region or film))	US-PGPUB; USPAT	AND	ON	2006/04/12 09:23
S113	0	(((quantum near2 well) or QW) with (strain$3 or stain$3)) and ((light ADJ3 emit$4 ADJ3 device) or (light-emit$4 ADJ3 device) or LED) and active and clad$4 and substrate and (barrier near3 (InGaP or InGaAsP or GaAsP)) and ((guide near2 (layer or medium or region or film)) with (Al with Ga with As))	US-PGPUB; USPAT	AND	ON	2006/04/12 09:27
S112	15	(((quantum near2 well) or QW) with (strain$3 or stain$3)) and ((light ADJ3 emit$4 ADJ3 device) or (light-emit$4 ADJ3 device) or LED) and active and clad$4 and substrate and (barrier near3 (InGaP or InGaAsP or GaAsP)) and ((guide near2 (layer or medium or region or film)) with (AlGaAs))	US-PGPUB; USPAT	AND	ON	2006/04/12 09:27
S111	0	(((quantum near2 well) or QW) with (strain$3 or stain$3)) and ((light ADJ3 emit$4 ADJ3 device) or (light-emit$4 ADJ3 device) or LED) and active and clad$4 and substrate and (barrier near3 (InGaP or InGaAsP or GaAsP)) and ((guide near2 (layer or medium or region or film)) with (Al with Ga with Ga))	US-PGPUB; USPAT	AND	ON	2006/04/12 09:27